





N-CHANNEL ENHANCEMENT MODE MOSFET

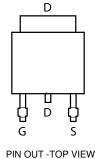
Features

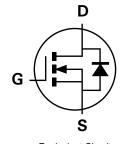
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: TO252-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.33 grams (approximate)







Top View

Equivalent Circuit

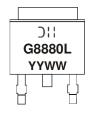
Ordering Information (Note 3)

Part Number	Case	Packaging
DMG8880LK3-13	TO252-3L	2500 / Tape & Reel

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



G8880L = Product Type Marking Code

| | = Manufacturer's Marking

| YYWW = Date Code Marking
| YY = Year (ex: 09 = 2009)

| WW = Week (01 ~ 53)



Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 4) V _{GS} = 10V	Steady State	$T_A = 25^{\circ}C$ $T_A = 85^{\circ}C$	I _D	11 8	Α
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	T _A = 25°C T _A = 85°C	I _D	16.5 12	А
Pulsed Drain Current (Note 6)	I _{DM}	48	Α		

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P _D	1.68	W
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 4)	$R_{\theta JA}$	74.3	°C/W
Power Dissipation (Note 5)	P _D	4.1	W
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 5)	$R_{\theta JA}$	30.8	°C/W
Operating and Storage Temperature Range	T_{J}, T_{STG}	-55 to +150	°C

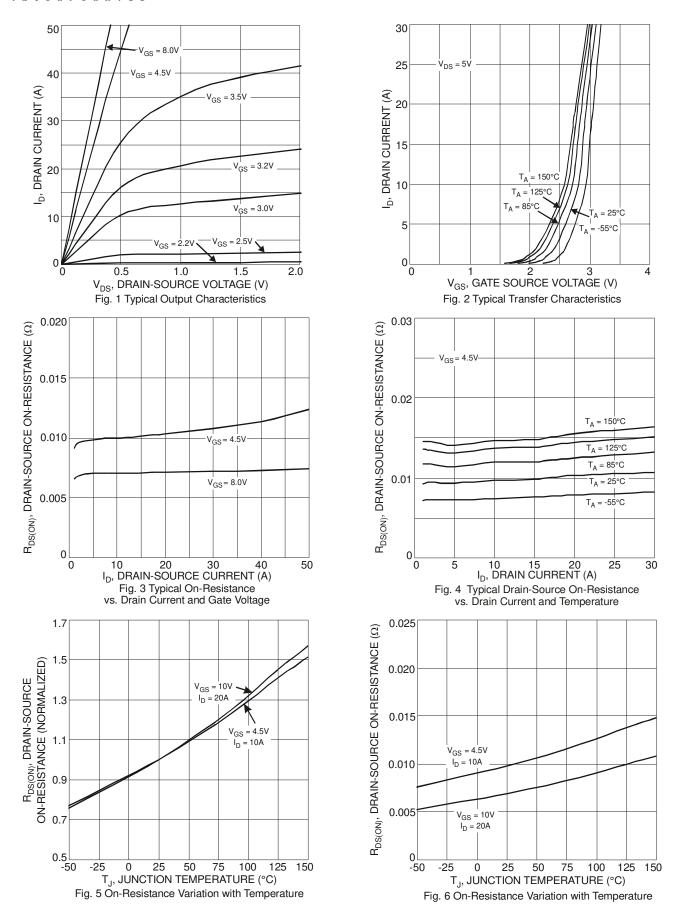
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	1	-	1.0	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	1.2	1.5	2.3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Bno (ON)		5 8	7.5 12	mΩ	$V_{GS} = 10V, I_D = 11.6A$	
Static Brain Source on resistance	R _{DS (ON)}				111.22	$V_{GS} = 4.5V, I_D = 10.7A$	
Forward Transfer Admittance	Y _{fs}	1	22	-	S	$V_{DS} = 15V, I_D = 15A$	
Diode Forward Voltage	V_{SD}	1	0.7	1.0	V	$V_{GS} = 0V, I_{SD} = 2.1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	-	1289	-	pF	V 45V V 0V	
Output Capacitance	Coss	-	187	-	pF	$V_{DS} = 15V, V_{GS} = 0V,$ -f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	-	162	-	pF	71 = 1.0IVID2	
Gate Resistance	Rg	-	0.97	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge at 10V	Qg	-	27.6	-	nC	V _{GS} = 10V, V _{DS} = 15V, I _D = 11.6A, Ig = 1.0mA	
Total Gate Charge at 5V	Qg	-	14.4	-	nC	V 5V V 45V	
Gate-Source Charge	Qgs	-	3.6	-	nC	$V_{GS} = 5V, V_{DS} = 15V,$	
Gate-Drain Charge	Q _{gd}	-	4.9	-	nC	I _D = 11.6A	
Turn-On Delay Time	t _{D(on)}	-	7.04	-	ns	$V_{DD} = 15V, V_{GS} = 10V,$ $R_{G} = 11\Omega, I_{D} = 11.6A,$ $R_{L} = 1.3\Omega$	
Turn-On Rise Time	t _r	-	17.52	-	ns		
Turn-Off Delay Time	t _{D(off)}	-	36.13	-	ns		
Turn-Off Fall Time	t _f	-	19.67	-	ns		
Body Diode Reverse Recovery Time	t _{rr}	-	17.6	-	ns	I _F = 20A, dl/dt = 500A/μs	
Body Diode Reverse Recovery Charge	Q _{rr}	-	65.9	-	nC	I _F = 20A, dl/dt = 500A/μs	

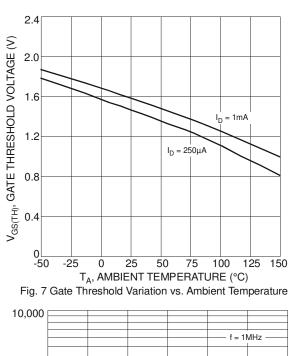
Notes:

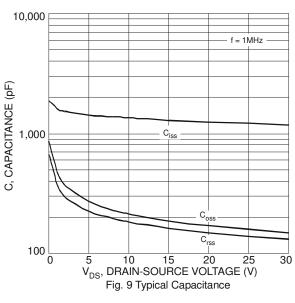
- 4. Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided.
 5. Device mounted on 2" x 2" FR-4 PCB with high coverage 2oz. copper, single sided.
 6. Repetitive rating, pulse width limited by junction temperature and current limited by package.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to production testing.

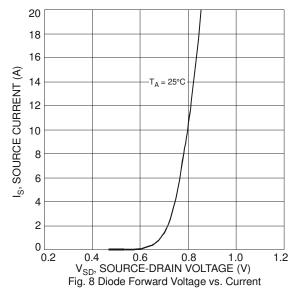


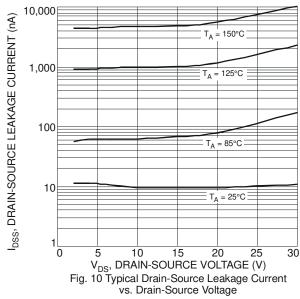


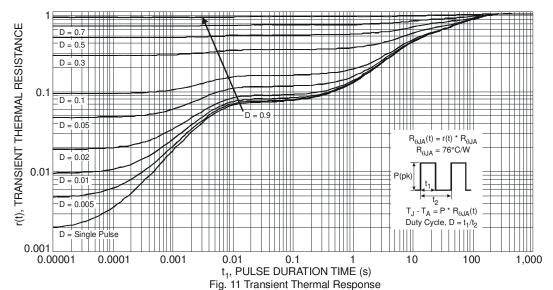






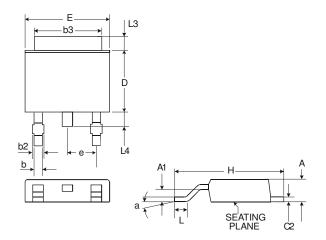






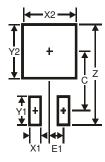


Package Outline Dimensions



TO252-3L					
Dim	Min	Тур	Max		
Α	2.19	2.29	2.39		
A1	0.97	1.07	1.17		
b	0.64	0.76	0.88		
b2	0.76	0.95	1.14		
b3	5.21	5.33	5.50		
C2	0.45	0.51	0.58		
D	6.00	6.10	6.20		
Е	6.45	6.58	6.70		
е	2.286 Typ.				
Н	9.40	9.91	10.41		
L	1.40	1.59	1.78		
L3	0.88	1.08	1.27		
L4	0.64	0.83	1.02		
а	0°	-	10°		
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
С	6.9
E1	2.3



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